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TABLE OF CONTENTS

DEVICE AND PROCESS

Session Co-Chairs: Krishna Shenai and Wendell Noble

| | | |
|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----|---|
| Trends for Deep Submicron VLSI and Their Implications for Reliability <i>P. Chatterjee, W. Hunter, A. Amerasekera, S. Aur, C. Duvvury, P. Nicollian, L. Ting, and P. Yang</i> | 1 | X |
| Reduced Poly-Si TFT Threshold Voltage Instability by High-Temperature Hydrogenation of a Si-Like Spin Centers <i>Y. Kamigaki, T. Hashimoto, M. Aoki, K. Yokogawa, M. Moniwa, S. Iijima, M. Minami, H. Ishida, H. Okuhira, S. Aoki, and T. Yamanaka</i> | 12 | X |
| Improving Program/Erase Endurance by Controlling the Inter-poly Process in Flash Memory <i>M. Ushiyama, H. Miura, H. Yashima, T. Adachi, T. Nishimoto, K. Komori, Y. Kamigaki, M. Kato, H. Kume, and Y. Ohji</i> | 18 | X |
| Impact of Shallow Trench Isolation on Reliability of Buried and Surface Channel sub- μ m PFET <i>W. Tonti, R. Bolam, and W. Hansch</i> | 24 | X |
| Reliability Improvement in High Aspect Ratio Contacts and Vias Filled with Blanket Tungsten CVD Film <i>N. Fukuda, T. Saito, Y. Suzuki, T. Fujiwara, H. Yamaguchi, and N. Owada</i> | 30 | |
| ON-State Programming and OFF-State Reliability of Metal-to-Metal Antifuse Based 10 nm-Thick SiNx Film For 3.3 V Operation <i>Y. Tamura and H. Shinriki</i> | 36 | |
| Model for the Leakage Instability in Unprogrammed Amorphous Silicon Antifuse Devices <i>P.E. Nicollian and W.R. Hunter</i> | 42 | |

HOT CARRIERS I: CHARACTERIZATION AND MODELING

Session Co-Chairs: Peng Fang and Eric Snyder

| | | |
|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|----|--|
| Impact of Velocity Saturation Region on nMOSFET's Hot-Carrier Reliability at Elevated Temperatures <i>H. Hwang, J.-S. Goo, H. Kwon, and H. Shin</i> | 48 | |
| Improved Lifetime Determination of Deep Submicron n-Channel MOSFETs using Charge Pumping Technique and Drain Current Degradation Modeling <i>D. Dorval, P. Dars, G. Merckel, and O. Bonnaud</i> | 51 | |
| Mechanism of ac-Stress-induced Leakage Current in EEPROM Tunnel Oxides <i>K. Shimizu, T. Endoh, and H. Iizuka</i> | 56 | |
| Characterization and Simulation of Hot-Carrier Effect on Erasing Gate Current in Flash EEPROMs <i>C. Huang, T. Wang, T. Chen, N.C. Peng, A. Chang, and F.C. Shone</i> | 61 | |
| Fast Timing Simulation for Submicron Hot-Carrier Degradation <i>W. Sun, E. Rosenbaum, and S.-M. Kang</i> | 65 | |
| Hot-Carrier-Induced Circuit Degradation In Actual DRAM <i>Y. Huh, D. Yang, H. Shin, and Y. Sung</i> | 72 | |

PACKAGING & MCM

Session Co-Chairs: Melissa Shell-De Guzman and Luu Nguyen

| | | |
|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------|----|--|
| Effects of Mold Compound Material Properties on Solder Reflow Package Cracking <i>S.K. Groothuis, K.G. Heinen, and L. Rimpillo</i> | 76 | |
| Critical Parameters for Achieving Optimum Reflow Profiles for Plastic Package Preconditioning <i>K.D. Hong, S.S. Lee, J.Y. Kim, S. Daniel, and C.K. Yoon</i> | 85 | |
| Modeling the Effect of Oxygen on the Fatigue Lifetime of Solder Joints <i>G. DiGiacomo</i> | 93 | |
| Polyimide Fatigue Induced Chip Surface Damage in DRAM's Lead-On-Chip (LOC) Packages <i>M. Amagai</i> | 97 | |

| | |
|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-------------------|
| Anomalous Thermal Conductivity in Regions of Non-Uniform Die Attach Integrity <i>W.A. Koziarz and D.A. Gilmour</i> | 107 |
| Evaluation of a Plastic Encapsulated Package Using a Scalable Thermal Mechanical Test Chip <i>A.K. Hullinger, J.M. Duffalo, A.J. Niederkorn, and N.J. Wecker</i> | 112 ^{2B} |
| A Novel Technique for Known Good Die Processing Eliminates Failure Mechanisms Caused by Traditional KGD Processing <i>P. Delivorias, R. Chrusciel, K. Rispoli, and S. Mango</i> | 116 |

DIELECTRICS

Session Co-Chairs: Bradley Moore and John Suehle

| | |
|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-------------------|
| TDDDB Characterisation of Thin SiO ₂ Films with Bimodal Failure Populations <i>J. Prendergast, J. Suehle, P. Chaparala, E. Murphy, and M. Stephenson</i> | 124 |
| Properties of High Voltage Stress Generated Traps in Thin Silicon Oxides <i>R.S. Scott, N.A. Dumin, T.W. Hughes, D.J. Dumin, and B.T. Moore</i> | 131 |
| The Relation between Oxide Degradation and Oxide Breakdown <i>C. Felsch and E. Rosenbaum</i> | 142 |
| Gate Oxide Breakdown Model in MOS Transistors <i>T.S. Yeoh, N.R. Kamat, R.S. Nair, and S.J. Hu</i> | 149 ^{3A} |
| Suppressed Process-Induced Damage in N ₂ O-Annealed SiO ₂ Gate Dielectrics <i>A.B. Joshi, R. Mann, L. Chung, M. Bhat, T.H. Cho, B.W. Min, and D.L. Kwong</i> | 156 |
| A Hot-Carrier Induced Low-Level Leakage Current in Thin Silicon Dioxide Films <i>N. Matsukawa, S. Yamada, K. Amemiya, and H. Hazama</i> | 162 |
| Electron Traps and Excess Current Induced by Hot-Hole Injection into Thin SiO ₂ Films <i>K. Kobayashi, A. Teramoto, and M. Hirayama</i> | 168 |

OPTOELECTRONICS AND COMPOUND SEMICONDUCTORS

Session Co-Chairs: Daniel Barton and Bill Roesch

| | |
|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-------------------|
| Categorizing Light Output Degradation Failures In LEDs Using The Relationship Between Defect Revealing Mechanisms Responsible for Electroluminescence (EL), Cathodoluminescence (CL), EBIC, and Reverse Bias Photoemission (RP) <i>R.S. Mann and D.K. McElfresh</i> | 177 |
| Reliability Purge Test of SAGCM InGaAs/InP APDs <i>N. Hwang, S.-G. Kang, H.-T. Lee, M.-K. Song, D.-G. Kim, and H.-M. Park</i> | 187 ^X |
| Degradation of Blue AlGaIn/InGaIn/GaN LEDs Subjected to High Current Pulses <i>D.L. Barton, J. Zeller, B.S. Phillips, P.-C. Chiu, S. Askar, D.-S. Lee, M. Osinski, and K. Malloy</i> | 191 ^{2B} |
| Reliability Assessment of Multiple Quantum Well Avalanche Photodiodes <i>I. Yun, H. Menkara, Y. Wang, I. Oguzman, J. Kolnik, K. Brennan, G. May, C. Summers, and B. Wagner</i> | 200 |
| Enhancement and Degradation of Drain Current in Pseudomorphic AlGaAs/InGaAs HEMTs Induced by Hot-Electrons <i>C. Canali, P. Cova, E. DeBortoli, F. Fantini, G. Meneghesso, R. Menozzi, and E. Zanoni</i> | 205 |
| Physical Mechanism of Performance Instabilities such as Kink Phenomena and Related Backgating Effect in GaAs MESFETs <i>K. Horio, K. Usami, and K. Satoh</i> | 212 |

FAILURE ANALYSIS

Session Co-Chairs: Shekhar Khandekar and Edward Cole

| | |
|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------------|
| DRAM Failure Analysis with the Force-Based Scanning Kelvin Probe <i>T. Hochwitz, A.K. Henning, C. Daghljan, R. Bolam, P. Coutu, R. Gluck, and J. Slinkman</i> | 217 |
| Recent Technology for Particle Detection on Patterned Wafers <i>M. Nozoe, M. Ikota, and N. Motomura</i> | 223 ^A |
| New Non-Bias Optical Beam Induced Current (NB-OBIC) Technique for Evaluation of Al Interconnects <i>T. Koyama, Y. Mashiko, M. Sekine, H. Koyama, and K. Horie</i> | 228 |
| OBIC Analysis of Stressed, Thermally-Isolated Polysilicon Resistors <i>E.I. Cole Jr., J.S. Suehle, K.A. Peterson, P. Chaparala, A.N. Campbell, E.S. Snyder, and D.G. Pierce</i> | 234 |

| | |
|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|
| Relation Between Etch Pit Pairs and Pipeline Defects in CMOS Device <i>S.H. Soh, J. Lari, S. Hunt, T. Davies, M. Kuo, U.S. Kim, M. Cheung, and E. Lucero</i> | 244 |
| New Latchup Failure Mechanism Induced by an Elevated Via Resistance on Multilayer CMOS Technology <i>Y.C. Chen, S. Hu, and T. DeBonis</i> | 249 |

HOT CARRIERS/ESD II: PHYSICS AND TECHNOLOGY

Session Co-Chairs: Kaizad Mistry and Faran Nouri

| | |
|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|
| Analysis and Optimisation of the Hot-Carrier Degradation Performance of 0.35- μ m Fully Overlapped LDD Devices <i>R. Bellens, P. Habas, G. Groeseneken, H.E. Maes, J.P. Mieville, G. Van den bosch, and L. Deferm</i> | 254 |
| Degraded CMOS Hot-Carrier Life Time—Role of Plasma Etching Induced Charging Damage and Edge Damage <i>X.Y. Li, T. Brozek, P. Aum, D. Chan, and C.R. Viswanathan</i> | 260 |
| On the Degradation Features of Poly-Emitter n-p-n BJTs After Hot-Carrier Injection <i>F. Maugain, C. Papadas, G. Ghibaudo, N. Gambetta, and P. Mortini</i> | 266 |
| Device Reliability and Optimization on Halo MOSFETs <i>D. Song, J. Lim, and K. Lee</i> | 271 |
| Building-in ESD/EOS Reliability for Sub-halfmicron CMOS Processes <i>C.H. Diaz, T.E. Kopley, and P.J. Marcoux</i> | 276 |
| EOS/ESD Reliability of Deep Sub-Micron NMOS Protection Devices <i>S. Ramaswamy, C. Duvvury, and S. Kang</i> | 284 |
| Water Diffusion Model for the Enhancement of Hot-Carrier-Induced Degradation due to Silicon Nitride Passivation in Submicron MOSFETs <i>M. Shimaya</i> | 292 |

BUILDING-IN RELIABILITY

Session Co-Chairs: Clyde Dunn and Rick Wachnik

| | |
|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|
| Boron Compounds as a Dominant Source of Alpha Particles in Semiconductor Devices <i>R. Baumann, T. Hossain, S. Murata, and H. Kitagawa</i> | 297 |
| Accurate Measurement of Small Charges Collected on Junctions from Alpha Particle Strikes Using an Accelerator-Produced Microbeam <i>T.J. Aton, J.A. Seitchik, S.D. Jantz, and H. Shichijo</i> | 303 |
| Design Rules for a Reliable Surface Micromachined IC Sensor <i>S. Bart, J. Chang, T. Core, L. Foster, A. Olney, S. Sherman, and W. Tsang</i> | 311 |
| An Accelerated Sodium Resistance Test for IC Passivation Films <i>C. Hong, B. Henson, T. Scelsi, and R. Hance</i> | 318 |

METALLIZATION

Session Co-Chairs: Biren Agarwala and John Yue

| | |
|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|-----|
| Impact of Test Structure Design on Electromigration Lifetime Measurements <i>L.M. Ting and C.D. Graas</i> | 326 |
| Temperature Measurement of Al Metallization and the Study of Black's Model in High Current Density <i>M. Sakimoto, T. Ito, T. Fujii, H. Yamaguchi, and K. Eguchi</i> | 333 |
| Effect of Al Alloy and Stacked Film Composition on Linewidth Dependence of Electromigration Lifetime <i>E.M. Atakov, J. Ling, J. Maziarz, A. Shepela, B. Miner, C. England, W. Harris, and D. Dunnell</i> | 342 |
| A New Analysis of Stress Relaxation Phenomenon for Stress-Migration Tolerance Estimation <i>Y. Kawano and T. Ohta</i> | 353 |
| Deoxidization of Water Desorbed from APCVD TEOS-O ₃ SiO ₂ by Titanium Cap Layer <i>M. Yoshimaru, T. Yoshie, M. Kageyama, K. Simokawa, Y. Fukuda, H. Onoda, and M. Ino</i> | 359 |
| An Increase of the Electromigration Reliability of Ohmic Contacts by Enhancing Backflow Effects <i>W. Zhang, Z.G. Li, Y.H. Cheng, W.L. Guo, Y. H. Sun, and X.X. Li</i> | 365 |
| Modeling Electromigration Failures in TiN/Al-alloy/TiN Interconnects and TiN Thin Films <i>J. Tao, N.W. Cheung, and C. Hu</i> | 371 |

| | |
|--------------------------------------------|-----|
| <i>Biographies</i> | 378 |
| <i>Index to Paper #</i> | 395 |
| <i>1995 Committees</i> | 396 |
| <i>IEEE Fellow Citation</i> | 401 |
| <i>Best Paper Award</i> | 402 |
| <i>Outstanding Paper Award</i> | 403 |
| <i>1995 Equipment Demonstrations</i> | 404 |